

Part Number		Customer		
Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Silicon Supplier	Topsil GW Only	Material Supplier
	2.0	Diameter	100.00 +/- 0.50 mm	
	3.0	Primary Flat Orientation	<110> +/- 1 degree	Wafer Vendor
	4.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	5.0	Secondary Flat Orientation	none/semi std	
	6.0	Overall Thickness	510.00 +/- 7.00 μ m	ADE 100%
	7.0	Total Thickness Variation (TTV)	<5.00 μ m	Guaranteed by Process
	8.0	Bow	<60.00 μ m	ADE to ASTM F534, 20%
	9.0	Warp	<60.00 μ m	ADE to ASTM F657, 20%
	10.0	Edge Chips	0	Bright Light, 100% (note 2)
	11.0	Edge Exclusion	5mm	
HandleSilicon	12.0	Handle Growth Method	CZ	Wafer Vendor - Topsil only
	13.0	Handle Orientation	{111} off 2.5 +/- 0.5 degree	Wafer Vendor
	14.0	Handle Thickness	415.00 +/- 5.00 μ m	ADE, 100%
	15.0	Handle Doping Type	N	Wafer Vendor
	16.0	Handle Dopant	Arsenic	Wafer Vendor
	17.0	Handle Resistivity	<0.003 Ohmcm	Wafer Vendor
	18.0	Backside Finish	Lapped and etched with lasermark and no oxide.	Wafer Vendor
	DeviceSilicon	19.0	Device Growth Method	FZ
20.0		Device Orientation	{111} off 3.5 +/- 0.5 degree	Wafer Vendor
21.0		Nominal Thickness	95.00 +/- 2.00 μ m	Filmetrics F50 XT, 100% 9-Pt (note3)
22.0		Distance to device silicon edge from wafer edge	< 2 mm	Guaranteed by Process
23.0		Device Doping Type	N	Wafer Vendor
24.0		Device Dopant	Phosphorous	Wafer Vendor
25.0		Device Resistivity	> 5000 Ohm-cm	Wafer Vendor
26.0		Buried Layer Implant	none	implant vendor
27.0		Voids	0	Bright Light, 100% (note 2)
28.0		Scratches	0	Bright Light, 100% (note 2)
29.0		Haze	none	Bright Light, 100% (note 2)

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Shipping Details	Wafer per box :	Max 25
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness



Explanatory Notes 1. Microscope inspection performed using microscope scan as below. 5x objective.

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information